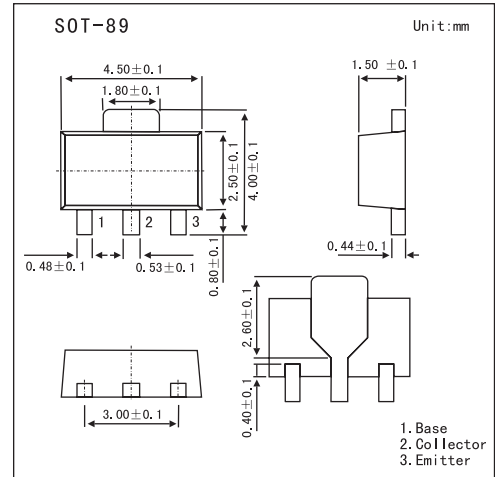


# 2SB1424

### Features

- Low  $V_{CE(sat)}$ .  $V_{CE(sat)} = -0.2V$  (Typ.) ( $I_C/I_B = -2A / -0.1A$ )
- Excellent DC current gain characteristics.
- PNP silicon transistor



### Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-20	V
Collector-emitter voltage	$V_{CEO}$	-20	V
Emitter-base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-3	A
	$I_{CP}^*$	-5	A
Collector dissipation	$P_C$	0.5	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\* Single pulse  $P_w=10ms$ .

### Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = -50\mu A$	-20			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = -1mA$	-20			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -50\mu A$	-6			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V$			-0.1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5V$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -2V, I_C = -0.1A$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C/I_B = -2A / -0.1A$			-0.5	V
Output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		35		pF
Transition frequency	$f_T$	$V_{CE} = -2V, I_E = 0.5A, f = 100MHz$		240		MHz

### $h_{FE}$ Classification

Marking	AEQ	AER
Rank	Q	R
$h_{FE}$	120~270	180~390